

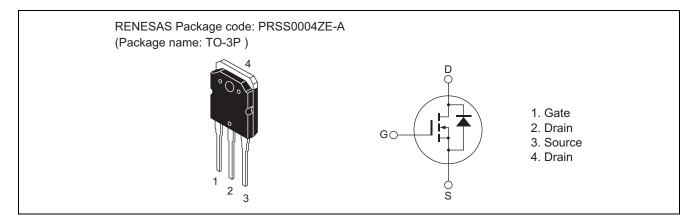
H5N2507P

250V - 50A - MOS FET High Speed Power Switching R07DS0877EJ0200 (Previous: RJJ03G0646-0100) Rev.2.00 Sep 12, 2012

Features

- Low on-resistance $R_{DS(on)} = 0.04~\Omega~typ.~(at~I_D = 25~A,~V_{GS} = 10~V,~Ta = 25^{\circ}C)$
- Low leakage current
- High speed switching
- Low gate charge
- Built-in fast recovery diode

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source voltage	V _{DSS}	250	V
Gate to Source voltage	V _{GSS}	±30	V
Drain current	I _D	50	Α
Drain peak current	I _{D (pulse)} Note1	200	Α
Body-Drain diode reverse Drain current	I _{DR}	50	Α
Avalanche current	I _{AP} Note3	35	Α
Channel dissipation	Pch Note2	150	W
Channel to case thermal impedance	θch-c	0.833	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

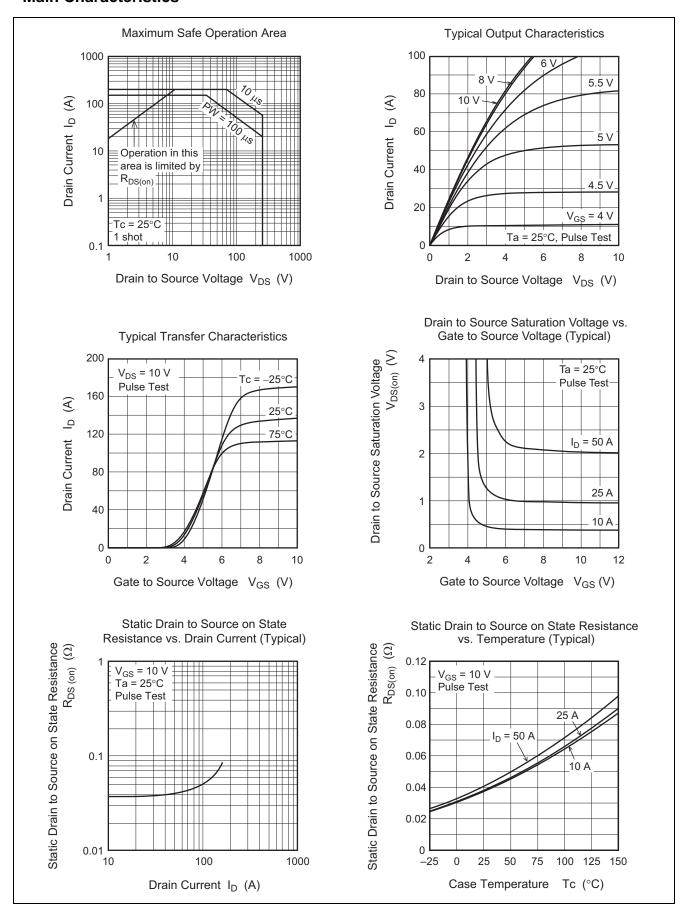
Electrical Characteristics

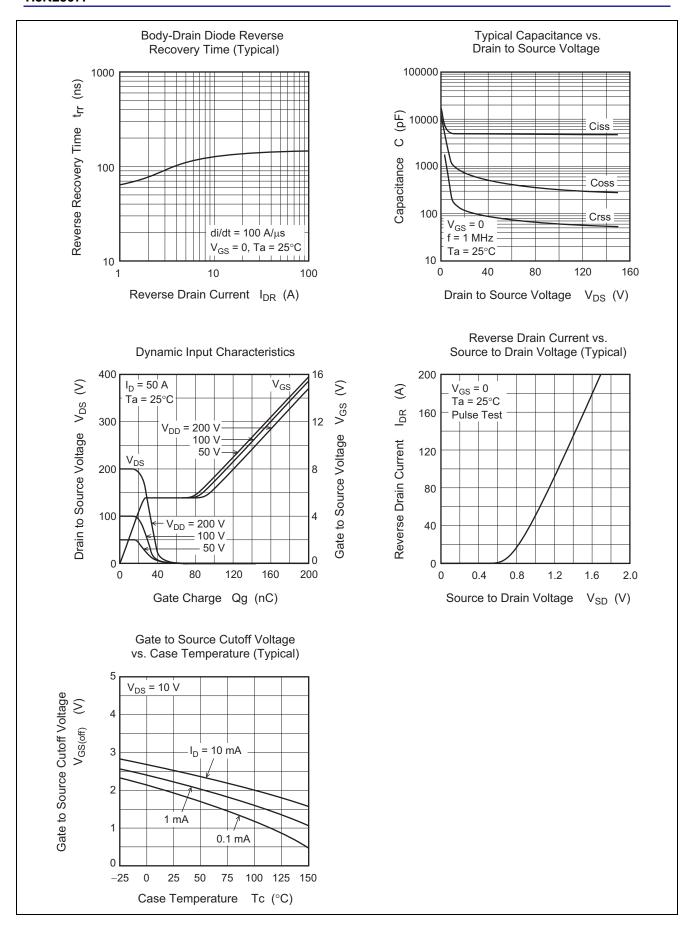
 $(Ta = 25^{\circ}C)$

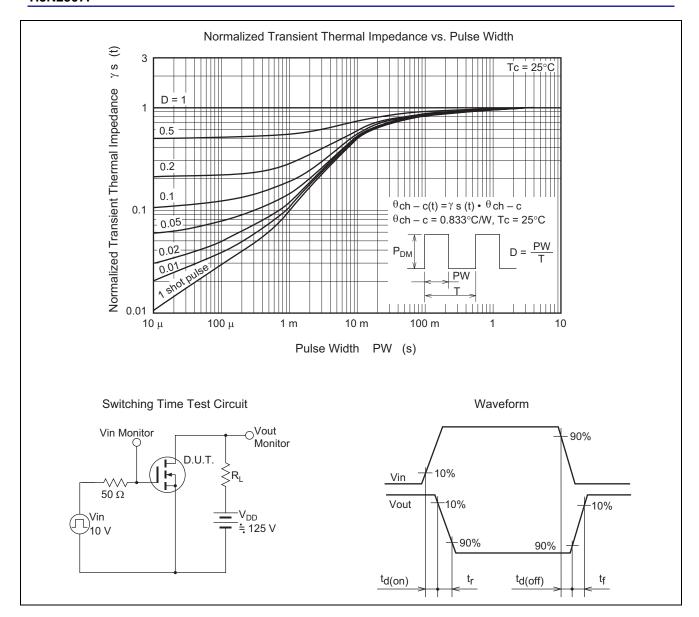
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	250	_		V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero Gate voltage Drain current	I _{DSS}		_	10	μΑ	$V_{DS} = 250 \text{ V}, V_{GS} = 0$
Gate to Source leak current	I _{GSS}		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to Source cutoff voltage	V _{GS(off)}	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static Drain to Source on state resistance	R _{DS(on)}	1	0.040	0.055	Ω	I _D = 25 A, V _{GS} = 10 V ^{Note4}
Forward transfer admittance	y _{fs}	20	36	l	S	$I_D = 25 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss		5000	l	pF	V _{DS} = 25 V
Output capacitance	Coss		640	l	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		105	_	pF	
Turn-on delay time	$t_{\text{d(on)}}$	_	55	_	ns	I_D = 25 A V_{GS} = 10 V R_L = 5 Ω Rg = 10 Ω
Rise time	t _r	_	200	_	ns	
Turn-off delay time	$t_{\text{d(off)}}$	_	250	_	ns	
Fall time	t _f	_	200	_	ns	
Total Gate charge	Qg	_	145	_	nC	V _{DD} = 200 V
Gate to Source charge	Qgs	_	25	_	nC	V _{GS} = 10 V I _D = 50 A
Gate to Drain charge	Qgd	_	65	_	nC	
Body-Drain diode forward voltage	V_{DF}	_	1.0	1.5	V	$I_F = 50 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-Drain diode reverse recovery time	t _{rr}	1	145	ı	ns	$I_F = 50 \text{ A}, V_{GS} = 0$ $di_F/dt = 100A/\mu s$
Body-Drain diode reverse recovery charge	Qrr	_	0.7	_	μС	

Note: 4. Pulse test

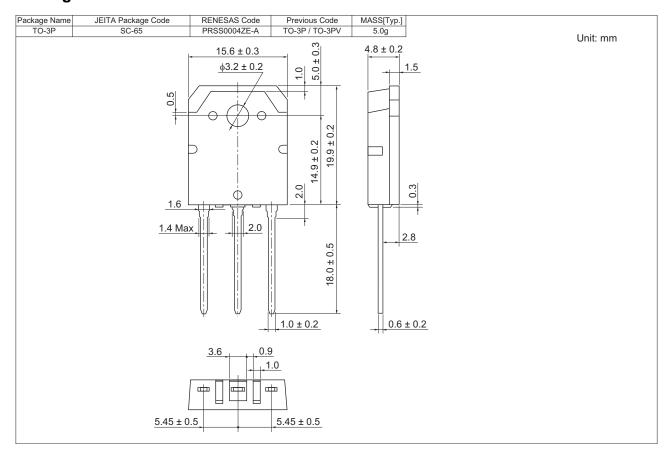
Main Characteristics







Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
H5N2507P	360 pcs	Box (Tube)

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